

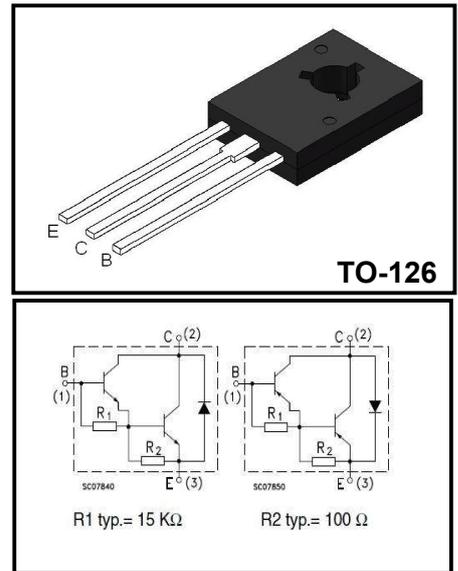
Plastic-EncapsulateDarlingtonTransistors
APPLICATION

◆Linear and switching industrial equipment.

DESCRIPTION

The BD675, BD675A, BD677, BD677A, BD679, BD679A and BD681 are silicon epitaxial-base NPN power transistors in monolithic Darlington configuration mounted in TO-126 plastic package. They are intended for use in medium power linear and switching applications.

The complementary PNP types are BD676, BD676A, BD678, BD678A, BD680, BD680A and BD682 respectively.

Absolute Maximum Ratings (Ta=25°C)


Symbol	Parameter	Value				Unit	
		NPN	BD675/A	BD677/A	BD679/A		BD681
BV _{CBO}	Collector-Base Voltage		45	60	80	100	V
BV _{CEO}	Collector-Emitter Voltage		45	60	80	100	V
BV _{EBO}	Emitter-Base Voltage		5				V
I _{CM}	Collector Current		4				A
P _D	Collector Power Dissipation		40				W
T _j , T _{stg}	Junction Temperature Storage Temperature		- 55 ~ + 150				°C

Electrical Characteristics (Ta=25°C)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	V _{CE} = rated V _{CBO} V _{CE} = rated V _{CBO} T _C = 100 °C			0.2 2	mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = half rated V _{CEO}			0.5	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			2	mA
BV _{CEO}	Collector-Emitter Sustaining Voltage	I _C = 50 mA for BD675/675A/676/676A for BD677/677A/678/678A for BD679/679A/680/680A for BD681/682	45 60 80 100			V
BV _{CBO}	Collector-Emitter Sustaining Voltage	I _C = 1 mA for BD675/675A/676/676A for BD677/677A/678/678A for BD679/679A/680/680A for BD681/682	45 60 80 100			V
H _{FE} *	DC Current Gain	for BD675/677/678/679/680/681/682 I _C = 1.5 A V _{CE} = 3 V for BD675A/677A/678A/679A/680A I _C = 2 A V _{CE} = 3 V	750 750			
V _{CESAT} *	Collector-Emitter Saturation Voltage	for BD677/678/679/680/681/682 I _C = 1.5 A I _B = 30 mA for BD677A/678A/679A/680A I _C = 2 A I _B = 40 mA			2.5 2.8	V
V _{BE} *	Base-Emitter Voltage	for BD675/677/678/679/680/681/682 I _C = 1.5 A V _{CE} = 3 V for BD675A/677A/678A/679A/680A I _C = 2 A V _{CE} = 3 V			2.5 2.5	V

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

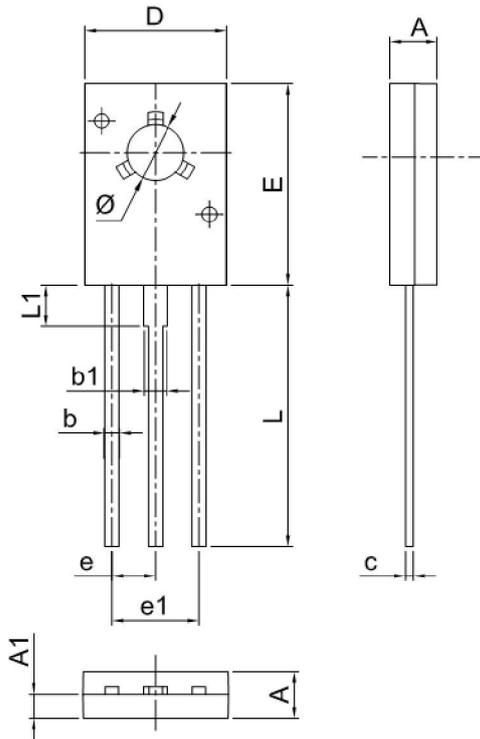
Ordering information

Package	Packing Description	Base Quantity
TO-126	Bulk	500pcs/Bag

Package Dimensions

TO-126

Symbol	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	2.40	2.80	0.094	0.110
A1	1.00	1.40	0.039	0.055
b	0.66	0.86	0.026	0.034
b1	1.17	1.37	0.046	0.054
c	0.40	0.60	0.016	0.024
D	7.30	7.70	0.287	0.303
E	10.60	11.00	0.417	0.433
e	2.25	2.33	0.089	0.092
e1	4.50	4.66	0.177	0.183
L	14.00	15.00	0.551	0.591
L1	1.90	2.50	0.075	0.098
Φ	3.10	3.30	0.122	0.130



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